

IN THE CLAIMS

Claim 1 (original): A method for manufacturing a semiconductor component, comprising:
providing a semiconductor substrate having a major surface;
forming first and second surface features over the major surface;
forming a first polysilicon layer over the first and second surface features; and
redistributing the first polysilicon layer in at least the region between the first and second surface features.

Claim 2 (original): The method of claim 1, wherein redistributing the first polysilicon layer comprises annealing the first polysilicon layer.

Claim 3 (original): The method of claim 2, wherein annealing the first polysilicon layer comprises annealing the first polysilicon in an ambient comprising hydrogen.

Claim 4 (original): The method of claim 3, wherein annealing the first polysilicon layer includes heating the first polysilicon layer to a temperature ranging between approximately 750 degrees Celsius and approximately 1,100 degrees Celsius.

Claim 5 (original): The method of claim 2, further including forming a second polysilicon layer over the first polysilicon layer.

Claim 6 (original): The method of claim 5, further including redistributing the second polysilicon layer.

Claim 7 (original): The method of claim 6, wherein redistributing the second polysilicon layer includes annealing the second polysilicon layer in a hydrogen ambient.

Claim 8 (original): The method of claim 7, wherein annealing the second polysilicon layer includes heating the second polysilicon layer to a temperature of at least 750 degrees Celsius.

Claim 9 (original): A method for manufacturing a semiconductor component, comprising:
providing a semiconductor substrate having a major surface;
forming a first dielectric material on the major surface;
forming first and second conductors over first and second portions of the first dielectric material, the first and second conductors having a gap therebetween;
forming a second dielectric material over the first and second conductors;
forming a first layer of polysilicon over the first and second conductors; and
repositioning atoms of the first layer of polysilicon.

Claim 10 (original): The method of claim 9, wherein forming the first and second conductors comprises:
forming a second layer of polysilicon over the first dielectric material; and
patterning the second layer of polysilicon over the first dielectric material to form the first and second conductors.

Claim 11 (original): The method of claim 9, wherein forming the first layer of polysilicon over the first and second conductors comprises forming a third dielectric material on the first and second conductors and forming the first layer of polysilicon on the third dielectric material.

Claim 12 (original): The method of claim 11, wherein repositioning atoms of the first layer of polysilicon comprises annealing the first layer of polysilicon.

Claim 13 (original): The method of claim 11, wherein repositioning atoms of the first layer of polysilicon comprises heating the first layer of polysilicon to a temperature of at least 750 degrees Celsius.

Claim 14 (original): The method of claim 11, further including forming a second layer of polysilicon over the first layer of polysilicon.

Claim 15 (original): The method of claim 14, further including annealing the second layer of polysilicon.

Claim 16 (original): The method of claim 11, wherein forming the first layer of polysilicon includes forming the first layer of polysilicon to have a thickness ranging between a monolayer of polysilicon and about 300 Angstroms.

Claim 17 (original): The method of claim 9, wherein repositioning atoms of the first layer of polysilicon includes repositioning the atoms in an ambient comprising hydrogen.

Claims 18-20 (canceled)